

depositing a second conductive layer on the surface after incorporating the oxygen-free material into the surface; and  
exposing the second conductive layer to a thermal process.

87. (New) The method in claim 86, wherein depositing a first conductive layer comprises depositing a capacitor plate and wherein the method further comprises depositing an insulator over the second conductive layer, and wherein exposing the second conductive layer to a thermal process comprises flowing the insulator.

88. (New) The method in claim 86, wherein the step of depositing a first conductive layer comprises depositing a plug and wherein exposing the second conductive layer to a thermal process comprises flowing the second conductive layer.

89. (New) The method in claim 36, wherein exposing the second conductive layer to a thermal process comprises exposing the second conductive layer to an alloy process.

90. (New) A method of forming a semiconductor device, comprising:  
depositing a tungsten nitride layer having a surface;  
incorporating a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof directly into the surface of the tungsten nitride layer to passivate the surface of the tungsten nitride layer to reduce an ability of the tungsten nitride layer to associate with oxygen;  
depositing a conductive layer on the surface of the tungsten nitride layer after incorporating the selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof into the surface of the tungsten nitride layer; and  
exposing the conductive layer to a thermal process.

91. (New) The method of claim 90 wherein depositing a tungsten nitride layer forms a capacitor plate and wherein the process further comprises depositing an insulator over the conductive layer and wherein exposing the conductive layer to a thermal process comprises flowing the insulator.

92. (New) The method of claim 90 wherein the conductive layer comprises copper.

93. (New) The method in claim 90 further comprising depositing a plug on which the tungsten nitride layer is thereafter deposited, and wherein exposing the conductive layer to a thermal process comprises flowing the conductive layer.

94. (New) The method in claim 90, wherein exposing the conductive layer to a thermal process comprises exposing the conductive layer to an alloy process.

95. (New) A method of forming a semiconductor device, comprising  
providing a first conductive layer having a surface and having an ability to associate with oxygen;

placing the surface of the first conductive layer in direct contact with a selection consisting of diborane, phosphine, methylsilane, hexamethyldisilane, hexamethyldisilazane, HCL, boron trichloride, and combinations thereof under appropriate conditions to passivate the surface and reduce the ability of the first conductive layer to associate with oxygen;

providing a second conductive layer on the surface of the first conductive layer; and

subjecting the second conductive layer to a thermal process.

96. (New) The method in claim 95 wherein depositing a first conductive layer forms a capacitor plate and wherein the process further comprises depositing an insulator over